

2N1026 Transistors

Si PNP Lo-Pwr BJT

Military/High-Rel N

V(BR)CEO (V) 35

V(BR)CBO (V) 40

I(C) Max. (A) 100m

Absolute Max. Power Diss. (W) 250m

Maximum Operating Temp (θ C) 175 \bar{o}

I(CBO) Max. (A) 25n

@V(CBO) (V) (Test Condition) 35

V(CE)sat Max. (V)

@I(C) (A) (Test Condition)

@I(B) (A) (Test Condition)

h(FE) Min. Current gain.

h(FE) Max. Current gain.

@I(C) (A) (Test Condition)

@V(CE) (V) (Test Condition)

f(T) Min. (Hz) Transition Freq 2.0M:

@I(C) (A) (Test Condition) 1.0m

@V(CE) (V) (Test Condition) 6.0

C(obo) (Max) (F) 7.0p

@V(CB) (V) (Test Condition) 6.0

@Freq. (Hz) (Test Condition)

Datasheet.Directory